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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		Application Number	09/976,983
(use as many sheets as necessary)		Filing Date	10/12/2001
		First Named Inventor	Xiawei Deng, et al.
		Group Art Unit	2518
		Examiner Name	PHAN
		Attorney Docket No.	T1-31071

U.S. PATENT DOCUMENTS					
Exam Initials*	Cite No.	U.S. Patent Document Number <sup>1</sup>	Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)
7P	AA	6,044,011		MARR et al.	03/26/2000
	AB				
	AC				
	AD				
	AE				
	AF				
	AG				
	AH				
	AI				
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FOREIGN PATENT DOCUMENTS						
Exam Initials*	Cite No.	Foreign Patent Document Office <sup>1</sup>	Number <sup>2</sup>	Kind Code <sup>3</sup> (if known)	Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)
	BA					
	BB					
	BC					
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	BE					
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS						
Exam Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-(page number(s)), publisher, city and/or country where published.				1*
7P	CA	NODA, K., et al., "A 1.8- $\mu$ m <sup>2</sup> Loadless CMOS Four-Transistor SRAM Cell in a 0.18- $\mu$ m Logic Technology," 1998 IEEE, pp. 643-646				
7P	CB	NODA, K., "An Ultra High Density High-Speed Loadless Four-Transistor SRAM Macro with a Dual-Layered Twisted Bit-Line and a Triple-Well Shield," 2000 IEEE Custom Integrated Circuits Conference, pp. 283-286				
7P	CC	TAKEDA, KOICHI, et al., "A 16Mb 400MHz Loadless CMOS Four-Transistor SRAM Macro," 2000 IEEE International Solid-State Circuits Conference, 2/8/2000, Digest of Technical Papers, pp. 264-265				
7P	CD	MASUOKA, S., et al., "A 0.99 $\mu$ m <sup>2</sup> Loadless Four-Transistor SRAM Cell in 0.13- $\mu$ m Generation CMOS Technology," IEEE 2000 Symposium on VLSI Technology, Digest of Technical Papers, pp. 164-165				
	CE					
	CF					
	CG					
	CH					
	CI					
	CJ					

Examiner Signature	Trang Phan	Date Considered	3/4/02
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